PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of Docket No: Q76643

Fumio MATSUMOTO

Appln. No.: 10/564,734 Group Art Unit: Unknown

Confirmation No.: 9627 Examiner: Unknown

Filed: January 17, 2006

For: InP SINGLE CRYSTAL, GaAs SINGLE CRYSTAL, AND METHOD FOR

PRODUCTION THEREOF

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §§ 1.97 and 1.98

MAIL STOP AMENDMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant hereby notifies the U.S. Patent and Trademark Office of the documents which are listed on the attached PTO/SB/08 A & B (modified) form and/or listed herein and which the Examiner may deem material to patentability of the claims of the above-identified application.

One copy of each of the listed documents is submitted herewith, except for the following: U.S. patents and/or U.S. patent publications; and co-pending non-provisional U.S. applications filed after June 30, 2003.

The present Information Disclosure Statement is being filed: (1) No later than three months from the application's filing date; (2) Before the mailing date of the first Office Action on the merits (whichever is later); or (3) Before the mailing date of the first Office Action after

INFORMATION DISCLOSURE STATEMENT

U.S. Appln. No.: 10/564,734

Attorney Docket No. Q76643

filing a request for continued examination (RCE) under §1.114, and therefore, no Statement

under 37 C.F.R. § 1.97(e) or fee under 37 C.F.R. § 1.17(p) is required.

In compliance with the concise explanation requirement under 37 C.F.R. § 1.98(a)(3) for

foreign language documents, Applicant submits the following explanations: English language

abstracts, submitted herewith, constitute concise statements of relevance for Japanese Patent

Application Publication Nos. 1-208396 and 3-40987. Further, a copy of an Office Action from

the Taiwanese Patent Office citing the listed JP-A-1-208396 in a corresponding Taiwanese

patent application is enclosed herewith. In addition, Applicant encloses an English language

translation of the listed Hoshikawa publication.

In the Information Disclosures Statement filed on January 17, 2006, nine documents were

listed. Applicant encloses herewith a copy of each of these documents.

The submission of the listed documents is not intended as an admission that any such

document constitutes prior art against the claims of the present application. Applicant does not

waive any right to take any action that would be appropriate to antedate or otherwise remove any

listed document as a competent reference against the claims of the present application.

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INFORMATION DISCLOSURE STATEMENT

U.S. Appln. No.: 10/564,734 Attorney Docket No. Q76643

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account.

Respectfully submitted,

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WASHINGTON OFFICE 23373
CUSTOMER NUMBER

Date: June 29, 2006

Substitute for Form 1449 A & B/PTO				Complete if Known		
				Application Number	10/564,734	
INFOR	MATION	DISCLOS	SURE	Confirmation Number	9627	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Filing Date	January 17, 2006	
				First Named Inventor	Fumio MATSUMOTO	
				Art Unit	Unknown	
				Examiner Name		
Sheet	1	of	1	Attorney Docket Number	Q76643	

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No.1	Document	Number	Publication Date MM-DD-YYYY		
		Number	Kind Code ² (if known)		Name of Patentee or Applicant of Cited Document	
		US				
		US				
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						FOREIGN PATENT DOCUMENTS							
Cite	Foreign Patent Document			Publication Date	Name of Patentee or								
No.1	Country Code ³	Number ⁴	Kind Code ⁵ (if known)	MM-DD-YYYY	Applicant of Cited Document	Translation ⁶							
	JP	1-208396	Α	08/22/1989	NIPPON MINING CO.	Abstract							
	JP	3-40987	A	02/21/1991	NIPPON TELEGR & TELEPH CORP.	Abstract							
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1	No.1	Code ³ JP	Code ³ Number Number 1-208396	Code ³ Number (if known) JP 1-208396 A	Code ³ Number (if known) JP 1-208396 A 08/22/1989	Code ³ Number (if known)							

NON PATENT LITERATURE DOCUMENTS							
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.					
		KEIGO HOSHIKAYA, "BULK CRYSTAL GROWING TECHNIQUE", ADVANCED ELECTRONICS SERIES I-4, PAGES 1-4 and PAGES 236-241	Yes				
		U. SAHR, "GROWTH OF S-DOPED 2" Inp-CRYSTALS BY THE VERTICAL GRADIENT FREEZE TECHNIQUE", 2001 INTERNATIONAL CONFERENCE ON INDIUM PHOSPHIDE AND RELATED MATERIALS CONFERENCE PROCEEDINGS, May 14-18, 2001, PAGES 533-536					

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Examiner Signature	Date Considered	
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^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or follow the hyperlink from the title of the document to the intranet. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to indicate here if English language Translation is attached.